

Silicon NPN Power Transistor

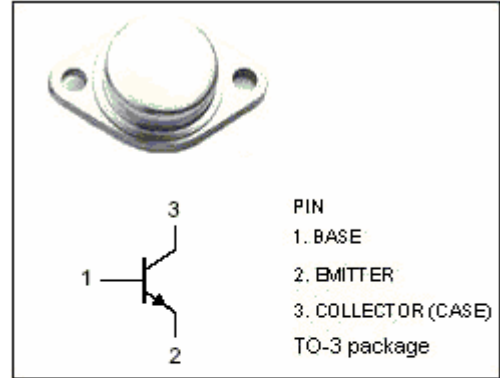
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DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 300V(\text{Min})$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 1.5V(\text{Max}) @ I_C = 2.5A$

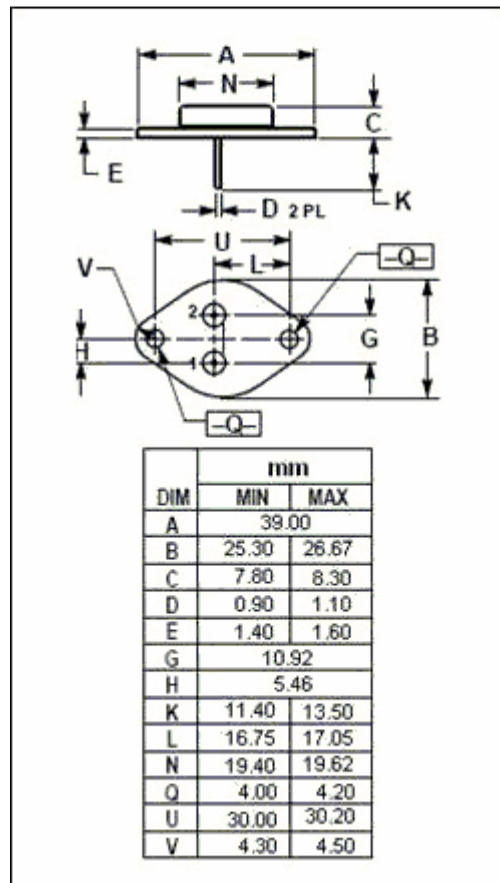
APPLICATIONS

- Designed for use in color TV receivers chopper supplies.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	6	A
I_{CM}	Collector Current-Peak Repetitive	8	A
I_B	Base Current	3	A
P_C	Collector Power Dissipation @ $T_C=25$	50	W
T_J	Junction Temperature	200	
T_{stg}	Storage Temperature Range	-65~200	



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ELECTRICAL CHARACTERISTICS

 $T_C=25$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100mA ; I_B=0$	200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1mA ; I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2.5A ; I_B=0.5A$			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2.5A ; I_B=0.5A$			1.4	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=400V ; I_E=0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6V ; I_C=0$			0.1	mA
f_T	Current-Gain—Bandwidth Product	$I_C=0.5A ; V_{CE}=10V$		10		MHz